

INTERNATIONAL SEARCH REPORT

International Application No

PCT/EP 03/03136

A. CLASSIFICATION OF SUBJECT MATTER
 IPC 7 C30B25/02 H01L21/205

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)
 IPC 7 C30B H01L

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the International search (name of data base and, where practical, search terms used)

INSPEC, EPO-Internal

C. DOCUMENTS CONSIDERED TO BE RELEVANT

| Category * | Citation of document, with indication, where appropriate, of the relevant passages | Relevant to claim No. |
|------------|--|-----------------------|
| X | <p>BAUER M ET AL: "Relaxed SiGe buffers with thicknesses below 0.1 mum" THIN SOLID FILMS, ELSEVIER-SEQUOIA S.A. LAUSANNE, CH, vol. 369, no. 1-2, July 2000 (2000-07), pages 152-156, XP004200345 ISSN: 0040-6090 cited in the application page 153, left-hand column, paragraph 2 -page 154, left-hand column, line 5</p> <p style="text-align: center;">-/-</p> | 18-22 |

 Further documents are listed in the continuation of box C. Patent family members are listed in annex.

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- *O* document referring to an oral disclosure, use, exhibition or other means
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Date of the actual completion of the International search

19 November 2003

Date of mailing of the International search report

27/11/2003

Name and mailing address of the ISA

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| International Application No PCT/EP 03/03136 |
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C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT

| Category ° | Citation of document, with indication, where appropriate, of the relevant passages | Relevant to claim No. |
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| A | HACKBARTH T ET AL: "Alternatives to thick MBE-grown relaxed SiGe buffers" THIN SOLID FILMS, ELSEVIER-SEQUOIA S.A. LAUSANNE, CH, vol. 369, no. 1-2, July 2000 (2000-07), pages 148-151, XP004200344 ISSN: 0040-6090 the whole document — | 1-22 |
| A | ROSENBLAD C ET AL: "A plasma process for ultrafast deposition of SiGe graded buffer layers" APPLIED PHYSICS LETTERS, AMERICAN INSTITUTE OF PHYSICS. NEW YORK, US, vol. 76, no. 4, 24 January 2000 (2000-01-24), pages 427-429, XP002200819 ISSN: 0003-6951 page 427, right-hand column, paragraph 2 —page 428, left-hand column, last line — | 1-22 |
| A | US 2002/056414 A1 (LEE SEUNG-YUN ET AL) 16 May 2002 (2002-05-16) paragraphs '0023!, '0026!, '0077!-'0079! — | 1-22 |
| A | US 2002/139996 A1 (JAGANNATHAN BASANTH) 3 October 2002 (2002-10-03) paragraphs '0027!, '0028! — | 1-22 |
| A | MUROTA J ET AL: "LOW-TEMPERATURE EPITAXIAL GROWTH OF Si/Si1-XGe/X HETEROSTRUCTURE BY CHEMICAL VAPOR DEPOSITION" JAPANESE JOURNAL OF APPLIED PHYSICS, PUBLICATION OFFICE JAPANESE JOURNAL OF APPLIED PHYSICS. TOKYO, JP, vol. 33, no. 4B, PART 1, 1 April 1994 (1994-04-01), pages 2290-2299, XP000595134 ISSN: 0021-4922 2. Ultraclean Low-Pressure CVD Processing; Figure 2 — | 1-22 |
| E | EP 1 315 199 A (ETH ZUERICH) 28 May 2003 (2003-05-28) cited in the application the whole document — | 1-22 |

INTERNATIONAL SEARCH REPORT

Information on patent family members

International application No

PCT/EP 03/03136

| Patent document cited in search report | | Publication date | | Patent family member(s) | | Publication date |
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| US 2002139996 | A1 | 03-10-2002 | JP | 2002324805 A | | 08-11-2002 |
| EP 1315199 | A | 28-05-2003 | EP WO | 1315199 A1 03044839 A2 | | 28-05-2003 30-05-2003 |